

## DUAL DAMASCENE PROCESS

### ABSTRACT

A dual damascene process is disclosed. According to the dual  
5 damascene process of the present invention, a first recessed region  
through an intermetal dielectric layer is filled with a bottom protecting  
layer, and the bottom protecting layer and the intermetal dielectric layer  
are simultaneously etched to form a second recessed region that has a  
shallower depth and wider width than the first recessed region on the  
10 first recessed region by using an etch gas selectively etches the  
intermetal dielectric layer with respect to the bottom protecting layer. In  
other words, the etch selectivity ratio, the intermetal dielectric layer with  
respect to the bottom protecting layer, is preferably about 0.5 to about  
1.5. Thus, it is possible to form a dual damascene structure without the  
15 formation of a byproduct or an oxide fence.